

## 54ABT543

# Octal Registered Transceiver with TRI-STATE® Outputs

## **General Description**

The 'ABT543 octal transceiver contains two sets of D-type latches for temporary storage of data flowing in either direction. Separate Latch Enable and Output Enable inputs are provided for each register to permit independent control of inputting and outputting in either direction of data flow.

- A and B outputs have current sourcing capability of 24 mA and current sinking capability of 48 mA
- Separate controls for data flow in each direction
- Guaranteed latchup protection
- High impedance glitch free bus loading during entire power up and power down cycle
- Nondestructive hot insertion capability
- Standard Military Drawing (SMD) 5962-9231401

### **Features**

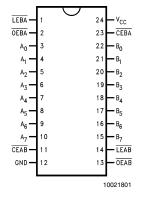
- Back-to-back registers for storage
- Bidirectional data path

### Ordering Code:

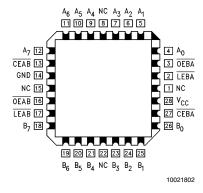
Military	Package	Package Description			
	Number				
54ABT543J-QML	J24F	24-Lead Ceramic Dual-In-Line			
54ABT543W-QML	W24C	24-Lead Cerpack			
54ABT543E-QML	E28A	28-Lead Ceramic Leadless Chip Carrier, Type C			

## **Connection Diagrams**

### Pin Assignment for **DIP and Flatpak**



### Pin Assianment for LCC



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### **Pin Descriptions**

Pin Names	Description		
OEAB, OEBA	Output Enable Inputs		
LEAB, LEBA	Latch Enable Inputs		
CEAB, CEBA	Chip Enable Inputs		
A <sub>0</sub> -A <sub>7</sub>	Side A Inputs or		
	TRI-STATE Outputs		
B <sub>0</sub> -B <sub>7</sub>	Side B Inputs or		
	TRI-STATE Outputs		

### **Functional Description**

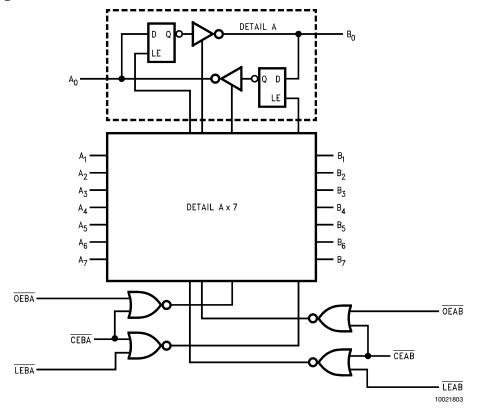
The 'ABT543 contains two sets of D-type latches, with separate input and output controls for each. For data flow from A to B, for example, the A to B Enable ( $\overline{CEAB}$ ) input must be low in order to enter data from the A port or take data from the B port as indicated in the Data I/O Control Table. With  $\overline{CEAB}$  low, a low signal on ( $\overline{LEAB}$ ) input makes the A to B latches transparent; a subsequent low to high transition of the  $\overline{LEAB}$  line puts the A latches in the storage mode and their outputs no longer change with the A inputs. With  $\overline{CEAB}$  and  $\overline{OEAB}$  both low, the B output buffers are active and reflect the data present on the output of the A latches. Control of data flow from B to A is similar, but using the  $\overline{CEBA}$  ,  $\overline{LEBA}$  and  $\overline{OEBA}$ .

#### Data I/O Control Table

Inputs			Latch Status	Output
CEAB	LEAB	OEAB		Buffers
Н	Χ	Χ	Latched	High Z
Х	Н	Χ	Latched	_
L	L	Χ	Transparent	_
Х	Χ	Н	_	High Z
L	Χ	L	_	Driving

H = High Voltage Level

### **Logic Diagram**



L = Low Voltage Level

X = Immaterial

### **Absolute Maximum Ratings** (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Storage Temperature  $-65^{\circ}\text{C}$  to  $+150^{\circ}\text{C}$ Ambient Temperature under Bias  $-55^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$ 

Junction Temperature under Bias

Ceramic -55°C to +175°C

 $\ensuremath{V_{\text{CC}}}$  Pin Potential to

Ground Pin -0.5V to +7.0V
Input Voltage (Note 2) -0.5V to +7.0V
Input Current (Note 2) -30 mA to +5.0

mA

Voltage Applied to Any Output

in the Disable or Power-Off State -0.5V to +5.5V in the HIGH State -0.5V to  $V_{CC}$ 

Current Applied to Output

in LOW State (Max) twice the rated  $I_{OL}$  (mA) DC Latchup Source Current -500 mA Over Voltage Latchup (I/O) 10V

# Recommended Operating Conditions

Free Air Ambient Temperature

Military  $-55^{\circ}$ C to  $+125^{\circ}$ C

Supply Voltage

Military +4.5V to +5.5V Minimum Input Edge Rate  $(\Delta V/\Delta t)$  Data Input 50 mV/ns Enable Input 20 mV/ns Clock Input 100 mV/ns

### **DC Electrical Characteristics**

Symbol	Parameter		ABT54	3	Units	V <sub>cc</sub>	Conditions
		Min	Тур	Max			
V <sub>IH</sub>	Input HIGH Voltage	2.0			V		Recognized HIGH Signal
V <sub>IL</sub>	Input LOW Voltage			0.8	V		Recognized LOW Signal
V <sub>CD</sub>	Input Clamp Diode Voltage			-1.2	V	Min	I <sub>IN</sub> = -18 mA (Non I/O Pins)
V <sub>OH</sub>	Output HIGH Voltage 54ABT	2.5					$I_{OH} = -3 \text{ mA}, (A_n, B_n)$
	54ABT	2.0			V	Min	$I_{OH} = -24 \text{ mA}, (A_n, B_n)$
V <sub>OL</sub>	Output LOW Voltage 54ABT			0.55	V	Min	$I_{OL} = 48 \text{ mA}, (A_n, B_n)$
V <sub>ID</sub>	Input Leakage Test	4.75			V	0.0	I <sub>ID</sub> = 1.9 μA, (Non-I/O Pins)
							All Other Pins Grounded
I <sub>IH</sub>	Input HIGH Current			5	μΑ	Max	V <sub>IN</sub> = 2.7V (Non-I/O Pins) (Note 3)
							V <sub>IN</sub> = V <sub>CC</sub> (Non-I/O Pins)
I <sub>BVI</sub>	Input HIGH Current Breakdown Test			7	μΑ	Max	V <sub>IN</sub> = 7.0V (Non-I/O Pins)
I <sub>BVIT</sub>	Input HIGH Current			100	μΑ	Max	$V_{IN} = 5.5V (A_n, B_n)$
	Breakdown Test (I/O)						
I <sub>IL</sub>	Input LOW Current			-5	μΑ	Max	V <sub>IN</sub> = 0.5V (Non-I/O Pins)(Note 3)
							V <sub>IN</sub> = 0.0V (Non-I/O Pins)
I <sub>IH</sub> + I <sub>OZH</sub>	Output Leakage Current			50	μΑ	0V-5.5V	$V_{OUT} = 2.7V (A_n, B_n);$
							OEAB or CEAB = 2V
I <sub>IL</sub> + I <sub>OZL</sub>	Output Leakage Current			-50	μΑ	0V-5.5V	$V_{OUT} = 0.5V (A_n, B_n);$
							OEAB or CEAB = 2V
Ios	Output Short-Circuit Current	-100		-275	mA	Max	$V_{OUT} = 0V (A_n, B_n)$
I <sub>CEX</sub>	Output HIGH Leakage Current			50	μΑ	Max	$V_{OUT} = V_{CC} (A_n, B_n)$
I <sub>ZZ</sub>	Bus Drainage Test			100	μΑ	0.0V	$V_{OUT} = 5.5V (A_n, B_n);$
							All Others GND
I <sub>CCLH</sub>	Power Supply Current			50	μΑ	Max	All Outputs HIGH
I <sub>CCL</sub>	Power Supply Current			30	mA	Max	All Outputs LOW
I <sub>CCZ</sub>	Power Supply Current			50	μΑ	Max	Outputs TRI-STATE
							All Others at V <sub>CC</sub> or GND

## DC Electrical Characteristics (Continued)

Symbol	Parameter	1	ABT543		Units	V <sub>cc</sub>	Conditions
		Min	Тур	Max			
I <sub>CCT</sub>	Additional I <sub>CC</sub> /Input			2.5	mA	Max	$V_I = V_{CC} - 2.1V$
							All Others at V <sub>CC</sub> or GND
I <sub>CCD</sub>	Dynamic I <sub>CC</sub> No Load						Outputs Open, CEAB
	(Note 3)			0.18	mA/MHz	Max	and OEAB = GND, CEBA =
							V <sub>CC</sub> , One Bit Toggling,
							50% Duty Cycle, (Note 4)

Note 1: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

Note 3: Guaranteed but not tested.

Note 4: For 8-bit toggling.  $I_{CCD}$  < 1.4 mA/MHz.

### **DC Electrical Characteristics**

						Conditions
Symbol	Parameter	Min	Max	Units	V <sub>cc</sub>	$C_L = 50 pF$ ,
						$R_L = 500\Omega$
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>		1.1	V	5.0	$T_A = 25^{\circ}C \text{ (Note 5)}$
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>		-0.45	V	5.0	$T_A = 25^{\circ}C(Note 5)$

Note 5: Max number of outputs defined as (n). n - 1 data inputs are driven 0V to 3V. One output at LOW.

### **AC Electrical Characteristics**

		54.	ABT		
		$T_A = -55^{\circ}$	C to +125°C		Fig.
Symbol	Parameter	V <sub>CC</sub> = 4	.5V-5.5V	Units	No.
		C <sub>L</sub> =	50 pF		
		Min	Max		
t <sub>PLH</sub>	Propagation Delay	1.6	6.4	ns	Figure 4
t <sub>PHL</sub>	$A_n$ to $B_n$ or $B_n$ to $A_n$	1.6	6.2		
t <sub>PLH</sub>	Propagation Delay				
t <sub>PHL</sub>	$\overline{\text{LEAB}}$ to $B_n$ , $\overline{\text{LEBA}}$ to $A_n$	1.6	6.6	ns	Figure 4
	OEBA or OEAB to A <sub>n</sub> or B <sub>n</sub>	1.6	6.4		
t <sub>PZH</sub>	Enable Time				
t <sub>PZL</sub>	$\overline{\text{LEAB}}$ to $B_n$ , $\overline{\text{LEBA}}$ to $A_n$	1.3	6.4	ns	Figure 6
	OEBA or OEAB to A <sub>n</sub> or B <sub>n</sub>	1.8	7.4		
t <sub>PHZ</sub>	Disable Time	2.0	7.2	ns	Figure 6
t <sub>PLZ</sub>	CEBA or CEAB to A <sub>n</sub> or B <sub>n</sub>	1.5	7.0		

# **AC Operating Requirements**

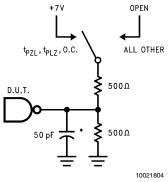
		54	ABT		
		$T_A = -55^{\circ}$	C to +125°C		Fig.
Symbol	Parameter	V <sub>CC</sub> = 4	.5V-5.5V	Units	No.
		C <sub>L</sub> =	50 pF		
		Min	Max		
t <sub>S</sub> (H)	Setup Time, HIGH or LOW	3.5		ns	Figure 7
t <sub>S</sub> (L)	$A_n$ or $B_n$ to $\overline{LEBA}$ or $\overline{LEAB}$	3.0			
t <sub>H</sub> (H)	Hold Time, HIGH or LOW	2.0		ns	Figure 7
t <sub>H</sub> (L)	A <sub>n</sub> or B <sub>n</sub> to LEBA or LEAB	2.0			
t <sub>S</sub> (H)	Setup Time, HIGH or LOW	3.3		ns	Figure 7
t <sub>S</sub> (L)	$A_n$ or $B_n$ to $\overline{CEAB}$ or $\overline{CEBA}$	2.5			
t <sub>H</sub> (H)	Hold Time, HIGH or LOW	2.0		ns	Figure 7
t <sub>H</sub> (L)	$A_n$ or $B_n$ to $\overline{CEAB}$ or $\overline{CEBA}$	2.0			
t <sub>W</sub> (L)	Pulse Width, LOW	3.5		ns	Figure 5

# Capacitance

Symbol Parameter		Тур	Units	Conditions: T <sub>A</sub> = 25°C	
C <sub>IN</sub>	Input Capacitance	5.0	pF	V <sub>CC</sub> = 0V (non I/O pins)	
C <sub>I/O</sub> (Note 6)	Output Capacitance	11.0	pF	$V_{CC} = 5.0V (A_n, B_n)$	

Note 6:  $C_{I/O}$  is measured at frequency, f = 1 MHz, PER MIL-STD-883, METHOD 3012.

## **AC** Loading



\*Includes jig and probe capacitance

FIGURE 1. Standard AC Test Load

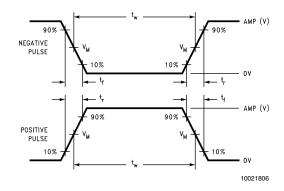


FIGURE 2.  $V_M = 1.5V$ Input Pulse Requirements

Amplitude	Rep. Rate	t <sub>w</sub>	t <sub>r</sub>	t <sub>f</sub>	
3V	1 MHz	500 ns	2.5 ns	2.5 ns	

FIGURE 3. Test Input Signal Requirements

## AC Loading (Continued)

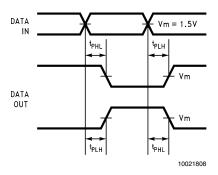


FIGURE 4. Propagation Delay Waveforms for Inverting and Non-Inverting Functions

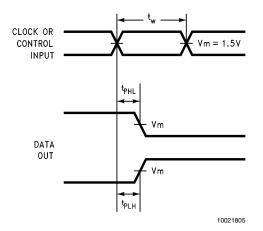


FIGURE 5. Propagation Delay, Pulse Width Waveforms

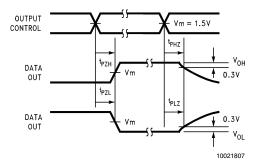


FIGURE 6. TRI-STATE Output HIGH and LOW Enable and Disable Times

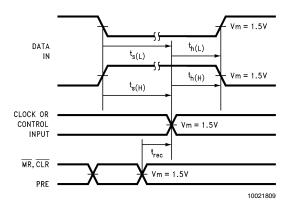
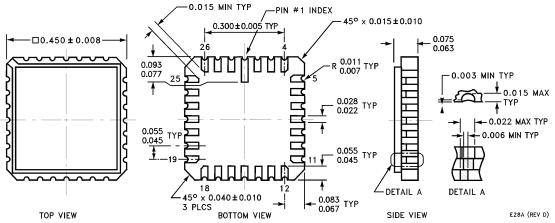
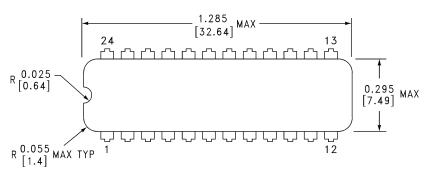


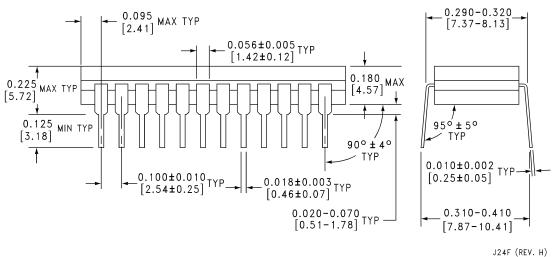
FIGURE 7. Setup Time, Hold Time and Recovery Time Waveforms

# **Physical Dimensions** inches (millimeters) unless otherwise noted



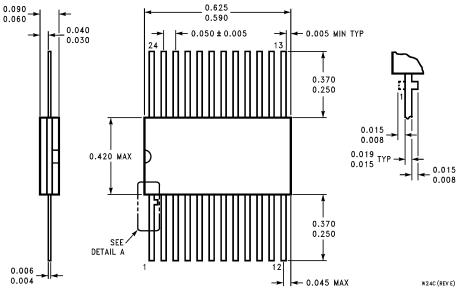
28-Lead Ceramic Leadless Chip Carrier (L) Order Number 54ABT543E-QML **NS Package Number E28A** 





24-Lead Ceramic Dual-In-Line Package Order Number 54ABT543J-QML NS Package Number J24F

### Physical Dimensions inches (millimeters) unless otherwise noted (Continued)



24-Lead Ceramic Flatpak Package (F) Order Number 54ABT543W-QML **NS Package Number W24C** 

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